Room-temperature current-induced magnetic switching and spintronic terahertz emission in all-vdW ferromagnetic heterostructure

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Abstract

Recent breakthroughs in two-dimensional (2D) ferromagnetic van der Waals (vdW) heterostructures have unlocked new potentials for spintronic applications. However, low-temperature ferromagnetic order due to the dimensional effect prohibits their widespread application. Here, we successfully fabricated wafer-scale two-dimensional ferromagnetic material FexGeTe2 by MBE, and the ferromagnetism of FexGeTe2 was significantly enhanced above room temperature by interfacial interaction [1] [2]. In an all-vdW heterostructure of FexGeTe2/Bi2Te3, we achieved a robust room-temperature spin-orbit torque (SOT) switching with lower power consumption [3]. Furthermore, we demonstrate the generation and optical detection of terahertz (THz) spin currents, setting a precedent for ultrafast THz spintronics [4]. Our work paves the way for advanced, high-speed spintronic devices designed for the challenges of modern electronics.

References

[1] Wang, H.T. et al. Interfacial engineering of ferromagnetism in wafer-scale van der Waals Fe₄GeTe₂ far above room temperature. Nat Commun 14, 2483 (2023).

[2] Wang H.Y. et al. Above Room-Temperature Ferromagnetism in Wafer-Scale Two-Dimensional van der Waals Fe₃GeTe₂ Tailored by a Topological Insulator. ACS Nano 14, 8, 10045–10053 (2020).

[3] Wang, H.Y. et al. Room temperature energy-efficient spin-orbit torque switching in twodimensional van der Waals Fe₃GeTe₂ induced by topological insulators. Nat Commun 14, 5173 (2023).

[4] Chen, X.H. et al. Generation and Control of Terahertz Spin Currents in Topology-Induced 2D Ferromagnetic Fe₃GeTe₂ | Bi₂Te₃ Heterostructures. Adv. Mater. 34, 2106172 (2022).